International
IOR Rectifier

Preliminary Data Sheet PD-20610 11/98

HF51A060ACE

Hexfred Die in Wafer Form

600 V
Size 51
5" Wafer

Electrical Characteristics (Wafer Form)

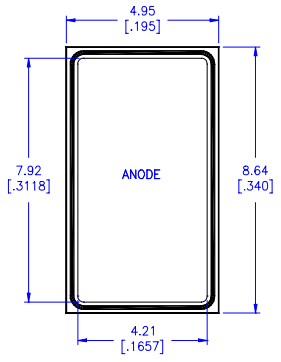
Parameter	Description	Guaranteed (Min/Max)	Test Conditions
V_{FM}	Forward Voltage	1.2V Max.	T_J = 25°C, I_F = 10.0A
BV_R	Reverse Breakdown Voltage	600V Min.	T_J = 25°C, I_R = 200µA
I_{RM}	Reverse Leakage Current	25µA Max.	T_J = 25°C, V_R = 600V

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr-Ni-Ag (1kA-4kA-6kA)
Nominal Front Metal Composition, Thickness	99% Al, 1% Si (3 microns)
Chip Dimensions	0.340" x 0.195"
Wafer Diameter	125mm, with std. < 100 > flat
Wafer Thickness	.015" ± .003"
Relevant Die Mechanical Dwg. Number	01-5312
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Recommended Storage Environment	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : IRG4PSC71KD

Die Outline



NOTES :
1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES)
2. CONTROLLING DIMENSION : (INCH)
3. DIMENSIONAL TOLERANCES :

BONDING PADS :	< 0.635 TOLERANCE = ± 0.013
WIDTH	< (.0250) TOLERANCE = ± (.0005)
&	> 0.635 TOLERANCE = ± 0.025
LENGTH	> (.0250) TOLERANCE = ± (.0010)
OVERALLDIE	< 1.270 TOLRANCE = ± 0.102
WIDTH	< (.050) TOLERANCE = ± (.004)
&	> 1.270 TOLERANCE = ± 0.203
LENGTH	> (.050) TOLERANCE = ± (.008)